

UPT5e3 – UPT48e3, UPT5Re3 – UPT48Re3 UPTB8e3 – UPTB48e3



SURFACE MOUNT TRANSIENT VOLTAGE SUPPRESSORS

DESCRIPTION

Microsemi's new Powermite UPT series of transient voltage suppressors feature oxide-passivated chips with high-temperature solder bonds for high surge capability and negligible electrical degradation under repeated surge conditions. Both unidirectional and bidirectional configurations are available. In addition to its size advantages, the Powermite package includes a fully metallic bottom (cathode) side that eliminates the possibility of solder flux entrapment at assembly and a unique locking tab serves as an integral heat sink. Its innovative design makes this device fully compatible for use with automatic insertion equipment. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- Powermite package with standoff voltages 5 to 48 V.
- Both unidirectional and bidirectional polarities:
 -Anode to case bottom (UPT5e3 thru UPT48e3)
 -Cathode to case bottom (UPT5Re3 thru UPT48Re3)
 -Bidirectional (UPTB8e3 thru UPTB48e3)
- Clamping time less than 100 pico-seconds for unidirectional and 5 nano-seconds for bidirectional version.
- Moisture classification is Level 1 with no dry pack required per IPC/JEDEC J-STD-020B.
 - RoHS compliant versions available.

APPLICATIONS / BENEFITS

- Protects sensitive components such as IC's, CMOS, Bipolar, BiCMOS, ECL, DTL, T²L, etc.
- Protection from switching and induced RF transients.
- New improved lower leakage current for the UPT5Re3:
 -Integral heat sink / locking tabs
 Fully matching heaten side climinates flux extrement
 - -Fully metallic bottom side eliminates flux entrapment
- Compliant to IEC61000-4-2 and IEC61000-4-4 for ESD and EFT protection respectively.
- Secondary lightning protection per IEC61000-4-5 with 42 Ohms source impedance:
 - Class 1: UPT5//UPT5R/UPTB8 to17
 - Class 2: UPT5//UPT5R/UPTB8 to12

MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value		Unit
Junction and Storage Temperature	T _J / T _{STG}	-65 to +150		°C
Thermal Resistance Junction-to-Ambient ⁽¹⁾	$R_{\Theta JA}$	240		°C/W
Thermal Resistance Junction-to-Case (base tab)	R _{ejc}	15		°C/W
Peak Pulse Power (see Figure 1 and Figure 2)		@ 8/20 µs	@10/1000µs	
UPT5Re3:	P _{PP}	600	100	
UPT5e3 thru UPT48e3:		1000	150	W
UPT8Re3 thru UPT48Re3:		1000	150	
UPTB8e3 thru UPTB48e3:		1000	150	
Steady-State Power Dissipation	PD	2.5		W
(base tab <u><</u> 112 ℃)				
Impulse Repetition Rate (duty factor)		0	.01	%
Solder Temperature @ 10 s	T _{SP}	260		°C

Notes: 1. When mounted on FR4 PC board with 1 oz copper.



DO-216AA Package

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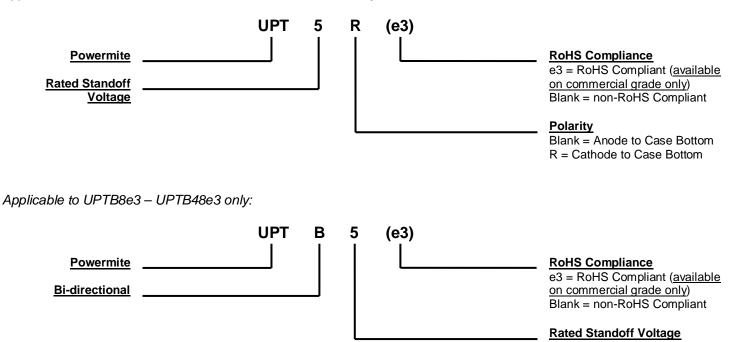


MECHANICAL and PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0.
- TERMINALS: Annealed matte-tin plating over copper and readily solderable per MIL-STD-750, method 2026.
- MARKING: Anode to TAB 1: T plus the last two digits of part number, e.g. UPT5e3 is T05•, UPT12e3 is T12• Cathode to TAB1: U plus last two digits of part number, e.g. UPT5Re3 is U05•, UPT12Re3 is U12• Bipolar: B plus the last two digits of part number, e.g. UPTB8e3 is B08•, UPTB12e3 is B12•, etc. Please note dot suffix (for e3 suffix)
- POLARITY: Cathode or anode to TAB 1 (bottom) as described in marking below and last page.
- TAPE & REEL option: Standard per EIA-481-B using 12 mm tape. Consult factory for quantities.
- WEIGHT: 0.016 gram (approximate).
- See Package Dimensions on last page.

PART NOMENCLATURE

Applicable to UPT5e3 – UPT48e3, UPT5Re3 – UPT48Re3 only:



SYMBOLS & DEFINITIONS				
Symbol	Definition			
V _(BR)	Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.			
V _{WM}	Working Peak Standoff Voltage: The maximum peak voltage that can be applied over the operating temperature range.			
P _{PP}	Peak Pulse Power: The peak power that can be applied for a specified pulse width and waveform.			
ID	Standby Current: The maximum current that will flow at the specified voltage and temperature.			
I _{PP}	Peak Pulse Current: The peak current that can be applied for a specified pulse width and waveform.			
С	Capacitance: The capacitance in picofarads of the TVS as defined @ 0 volts at a frequency of 1 MHz.			



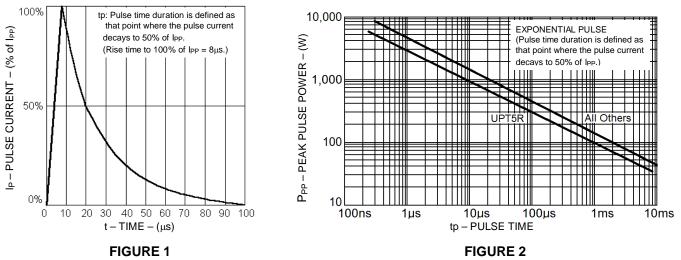
ELECTRICAL CHARACTERISTICS

DEVICE T (add e3 su		RATED STANDOFF VOLTAGE V _{VM}	MINIMUM BREAKDOWN VOLTAGE V _(BR) @ 1 mA	MAXIMUM STANDBY CURRENT I _D @V _{WM}	MAXIMUM PEAK PULSE CURRENT* Ι _{ΡΡ} @ 8/20 μs	MAXIMUM CLAMPING VOLTAGE V _C @ 10A*	MAXIMUM TEMPERATURE COEFFICIENT of V _(BR) α _{V(BR)}
Unidirectional	Bi-directional	V	V	μA	Α	V	%/°C
UPT5		5	6.0	50	89.4	9.5	.030
UPT5R		5	6.0	5	60	9.5	.030
UPT8 & UPT8R	UPTB8	8	9.0	2	62.1	13.7	.040
UPT10 & UPT10R	UPTB10	10	11.0	2	47.2	18.0	.045
UPT12 &UPT12R	UPTB12	12	13.8	1	40.3	21.6	.050
UPT15 & UPT15R	UPTB15	15	16.7	1	33.9	26.0	.055
UPT17 & UPT17R	UPTB17	17	19.0	1	30.8	29.2	.060
UPT24 & UPT24R	UPTB24	24	28.4	1	22.0	43.2	.070
UPT28 &UPT28R	UPTB28	28	31.0	1	19.2	47.8	.075
UPT33 &UPT33R	UPTB33	33	36.8	1	16.4	56.7	.080
UPT48 &UPT48R	UPTB48	48	54.0	1	11.2	84.3	.090

* See Figure 1 for I_{PP} waveform of 8/20 µs.

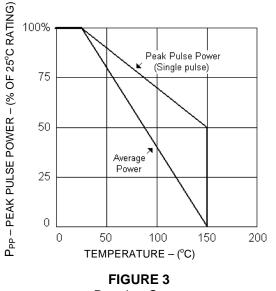


GRAPHS

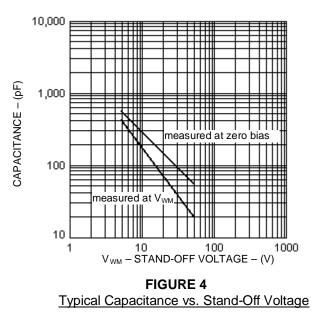






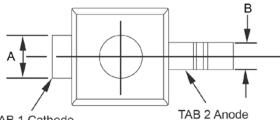


Derating Curve

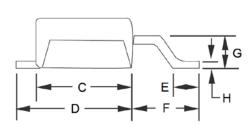


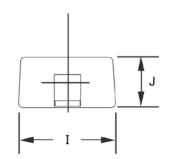


PACKAGE DIMENSIONS



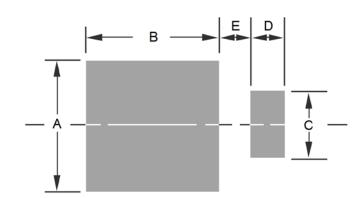






	Dimensions					
Ltr	Ltr Inch		Millimeters			
	Min	Max	Min	Max		
Α	0.73	0.99	0.029	0.039		
В	0.40	0.66	0.016	0.026		
С	1.77	2.03	0.070	0.080		
D	2.21	2.46	0.087	0.097		
E	0.50	0.76	0.020	0.030		
F	1.29	1.54	0.051	0.061		
G	0.53	0.78	0.021	0.031		
Н	0.10	0.20	0.004	0.008		
I	1.77	2.03	0.070	0.080		
J	0.89	1.14	0.035	0.045		

PAD LAYOUT



	Dimensions			
Ltr	Inch	Millimeters		
Α	0.100	2.54		
В	0.105	2.67		
С	0.050	1.27		
D	0.030	0.76		
E	0.025	0.64		